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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/910,447	07/19/2001	Toshihiko Higuchi	81754.0064	2754
26021	7590	10/29/2003	EXAMINER	
HOGAN & HARTSON L.L.P. 500 S. GRAND AVENUE SUITE 1900 LOS ANGELES, CA 90071-2611			LE, THAO X	
			ART UNIT	PAPER NUMBER
			2814	

DATE MAILED: 10/29/2003

Please find below and/or attached an Office communication concerning this application or proceeding.

<b>Office Action Summary</b>	<b>Application No.</b>	<b>Applicant(s)</b>	
	09/910,447	HIGUCHI, TOSHIHIKO	
	<b>Examiner</b>	<b>Art Unit</b>	
	Thao X Le	2814	

-- **Th MAILING DATE of this communication appears on the cover sheet with the correspondenc address --**  
**Period for Reply**

**A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.**

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133).
- Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

**Status**

- 1) ☒ Responsive to communication(s) filed on 22 September 2003.
- 2a) ☒ This action is **FINAL**.                      2b) ☐ This action is non-final.
- 3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

**Disposition of Claims**

- 4) ☒ Claim(s) 1-4, 7, 9, 11, 21-24, 28, 29, 31, 32, 34-36, 38-40 and 42-63 is/are pending in the application.
- 4a) Of the above claim(s) \_\_\_\_\_ is/are withdrawn from consideration.
- 5) ☐ Claim(s) \_\_\_\_\_ is/are allowed.
- 6) ☒ Claim(s) 1-4, 7, 9, 11, 21-24, 28-29, 31-32, 34-36, 38-40, 42-63 is/are rejected.
- 7) ☐ Claim(s) \_\_\_\_\_ is/are objected to.
- 8) ☐ Claim(s) \_\_\_\_\_ are subject to restriction and/or election requirement.

**Application Papers**

- 9) ☐ The specification is objected to by the Examiner.
- 10) ☐ The drawing(s) filed on \_\_\_\_\_ is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.  
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
- 11) ☐ The proposed drawing correction filed on \_\_\_\_\_ is: a) ☐ approved b) ☐ disapproved by the Examiner.  
If approved, corrected drawings are required in reply to this Office action.
- 12) ☐ The oath or declaration is objected to by the Examiner.

**Priority under 35 U.S.C. §§ 119 and 120**

- 13) ☐ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).  
a) ☐ All b) ☐ Some \* c) ☐ None of:  
1. ☐ Certified copies of the priority documents have been received.  
2. ☐ Certified copies of the priority documents have been received in Application No. \_\_\_\_\_.  
3. ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).  
\* See the attached detailed Office action for a list of the certified copies not received.
- 14) ☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. § 119(e) (to a provisional application).  
a) ☐ The translation of the foreign language provisional application has been received.
- 15) ☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. §§ 120 and/or 121.

**Attachment(s)**

- |  |   |
|--|---|
| 1) <input checked="" type="checkbox"/> Notice of References Cited (PTO-892)                  | 4) <input type="checkbox"/> Interview Summary (PTO-413) Paper No(s). _____  |
| 2) <input type="checkbox"/> Notice of Draftsperson's Patent Drawing Review (PTO-948)         | 5) <input type="checkbox"/> Notice of Informal Patent Application (PTO-152) |
| 3) <input type="checkbox"/> Information Disclosure Statement(s) (PTO-1449) Paper No(s) _____ | 6) <input type="checkbox"/> Other: _____                                    |

## DETAILED ACTION

### *Claim Rejections - 35 USC § 102*

1. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless –

(e) the invention was described in–

(1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effect under this subsection of a national application published under section 122(b) only if the international application designating the United States was published under Article 21(2)(a) of such treaty in the English language; or

(2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that a patent shall not be deemed filed in the United States for the purposes of this subsection based on the filing of an international application filed under the treaty defined in section 351(a).

2. Claims 1-4, 7, 32, 36, 44-48, 50, 56-60 are rejected under 35 U.S.C. 102(e) as being anticipated by US 6201278 to Gardner et al.

Regarding claims 1, 32, Gardner discloses a semiconductor device in fig. 1A-5K comprising: a semiconductor substrate 502 (or 102), column 12 line 62, having a indented section 514, fig. 5D, a gate dielectric 524 (or 124), column 13 line 57, disposed on the indented section, fig. 5H, a gate electrode 530 (or 130), column 13 line 66, disposed on the gate dielectric layer 524, wherein a portion of the gate electrode 530 is embedded in the semiconductor substrate 502 and another portion of the gate electrode is above the semiconductor substrate (the semiconductor substrate comprises a top surface 504 and oxide layers 526A/526B, the gate electrode 530 shows above the top surface 504) first and second impurity diffusion layers 508A and 508B, column 13 line 49, disposed in the semiconductor substrate and opposed to each other with the gate electrode being interposed between them, a third impurity diffusion layer P-, fig. 5G, disposed in a portion immediately below the gate electrode in the semiconductor substrate, a

sidewall dielectric layer 522A and 522B, column 13 line 38, disposed on the side surface section of the gate electrode 530, wherein the gate electrode has a width that gradually increases from a bottom thereof up to an upper surface thereof, and wherein surfaces of the first and second impurity diffusion layers are located at a position higher than an interface between the semiconductor substrate and the gate dielectric layer, fig. 5K or 1J.

Regarding to claim 2, Gardner discloses the semiconductor device wherein a distance between the surface of the first and second impurity diffusion layers and the interface between the semiconductor substrate and the gate dielectric between about 0.20  $\mu\text{m}$ , column 3 line 10.

Regarding to claim 3, Gardner discloses a semiconductor device wherein the groove section 514, column 13 line 11, is disposed at a specified location in the semiconductor substrate, and the gate electrode 530 is disposed on a bottom surface of the groove section through the gate dielectric layer 524, fig 5a-5K.

Regarding to claims 4, 7, Gardner discloses a semiconductor device wherein the gate electrode 530 may be disposed by depositing the conductive material or semiconductor material, at least one alloy that includes at least two constituents selected from polycrystalline silicon, tungsten, tantalum, copper and gold, column 13 line 66 and column 14 line 61, wherein the first and second impurity diffusion layers include an extension 552A/552B, fig. 5K.

Regarding to claim 32, Gardner discloses a semiconductor device in fig. 5A-5K comprising: a semiconductor substrate 502, column 12 line 62, a groove section 514, fig. 5D, formed at a specified location in the semiconductor substrate, a gate electrode 530, column 13 line 66, formed on a bottom surface of the groove section through a gate dielectric layer 524, wherein the gate electrode has a width that gradually increases from a bottom thereof toward an

upper surface thereof, and a width of the upper surface of the gate electrode substantially equals to a width of the groove, fig. 5K.

Regarding claim 36, Gardner discloses the extension regions 132A/132B are below the sidewall dielectric layer, and wherein an area below the gate dielectric layer is free of the extension regions, fig. 1J.

Regarding claims 44-48, 50, 56-60 Gardner discloses the gate electrode 130 has a width the continuously increase from the bottom thereof up to an upper surface thereof, wherein the semiconductor substrate has a first surface and the indented section 114, fig. 1D, has a second surface below the first surface, and wherein the entire gate dielectric layer 124 is disposed on the second surface, wherein the sidewall 122A/122B dielectric layer and the gate dielectric layer 124 are disposed in contact with the indented section.47, wherein the sidewall dielectric layer has an outer surface that is substantially vertical with respect to the first surface of the semiconductor substrate, wherein the sidewall dielectric layer 122A/122B surrounds the gate dielectric layer 124, and wherein at least a portion of the gate dielectric layer is above at least a portion of the sidewall dielectric layer.

### ***Claim Rejections - 35 USC § 103***

3. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

4. Claims 9, 11, 21-24, 28-29, 31, 34-35, 39-40, 42-43, 49-55, and 61-63, are rejected under 35 U.S.C. 103(a) as being unpatentable over US 6201278 to Gardner et al in view of US 6214679 to Murthy et al.

Regarding claims 9, 29, 61, Gardner does not expressly disclose the semiconductor device wherein the first metal silicide layer is disposed on the first and second impurity diffusion layers, and the gate electrode includes a second metal silicide layer on an upper surface thereof.

But Murthy reference discloses the semiconductor device wherein the metal silicide layer 236 is formed on the first and second impurity diffusion layers 218, and the gate electrode 206 includes a metal silicide layer 236, fig. 12, on an upper surface thereof. At the time the invention was made; it would have been obvious to one of ordinary skill in the art to use silicide layer teaching of Murthy with Gardner, because it would have reduced the resistance of polysilicon as taught by Murthy, column 1 line 47-48.

Regarding claims 11, 62, Gardner does not expressly disclose the semiconductor device wherein the surface of the first and second impurity diffusion layers are formed at a position higher than a surface of the STI.

But Murthy reference discloses the semiconductor device in fig. 12 wherein the surface of the first and second impurity diffusion layers 218 are formed at a position higher than a surface of the STI. At the time the invention was made; it would have been obvious to one of ordinary skill in the art to use the elevated source and drain teaching of Murthy with Gardner's device, because it would have increased the conductivity and good punch through characteristics obtained as taught by Murthy, column 5 line 62-67.

Regarding claim 21, as discussed in the above claim 1 Gardner discloses all the limitations of claim 21, except the surface of the first and second impurity diffusion layers are disposed at a position higher than a surface of the STI.

But Murthy reference discloses the semiconductor device in fig. 12 wherein the surface of the first and second impurity diffusion layers 218 are formed at a position higher than a surface of the STI. At the time the invention was made; it would have been obvious to one of ordinary skill in the art to use the elevated source and drain teaching of Murthy with Gardner's device, because it would have increased the conductivity and good punch through characteristics obtained as taught by Murthy, column 5 line 62-67.

Regarding claims 22-24, 28, and 31, Gardner discloses the semiconductor device wherein a distance between the surface of the first and second impurity diffusion layers and the interface between the semiconductor substrate and the gate dielectric between about 0.20  $\mu\text{m}$ , column 3 line 10 (channel length), wherein the groove section 514, column 13 line 11, is disposed at a specified location in the semiconductor substrate, and the gate electrode 530 is disposed on a bottom surface of the groove section through the gate dielectric layer 524, fig 5a-5K, wherein the gate electrode 530 is disposed from at least one alloy that includes at least two constituents selected from polycrystalline silicon, tungsten, tantalum, copper and gold, column 13 line 66 and column 14 line 61, wherein the a third impurity diffusion layer P-, fig. 5J, immediately below the gate electrode in the semiconductor substrate, and wherein the first and second impurity diffusion include an extension region N', fig. 1J or 5K wherein the sidewall dielectric layer 522A/522B is formed from a material including silicon oxide, column 13 line 38, wherein the sidewall dielectric layer 522A/522B or 122A/122B has an outer surface that is generally vertical

with respect to the surface of the semiconductor substrate, and film thickness that gradually reduces from a bottom thereof up to an upper surface thereof, fig. 1J and 5K.

Regarding claims 34, 38, and 63, Gardner does not expressly disclose a semiconductor device wherein a majority of the gate electrode is above the semiconductor surface and the first and second impurity diffusion layers.

However, Gardner discloses a semiconductor device wherein the gate electrode is above the semiconductor surface and the first and second impurity diffusion layers.

Accordingly, it would have been obvious to one of ordinary skill in art to use teaching of Gardner in the range as claimed, because it has been held that where the general conditions of the claims are disclosed in the prior art, it is not inventive to discover the optimum or workable range by routine experimentation. See *In re Aller*, 220 F.2d 454, 105 USPQ 233, 235 (CCPA 1955).

Regarding claims 35, 39, 40, 42-43, Gardner discloses the semiconductor device wherein the third impurity diffusion layer P- is completely disposed between the first and second impurity diffusion layers, fig. 1J or 5K, wherein the extension regions 132A/132B are below the sidewall dielectric layer, and wherein an area below the gate dielectric layer is free of the extension regions, fig. 1J.

Regarding claims 49-55, Gardner discloses the semiconductor device wherein at least a portion of the gate dielectric layer is above at least a portion of the sidewall dielectric layers and wherein the sidewall dielectric layer 122A is formed below the second metal silicide layer, wherein a the gate electrode is above the semiconductor substrate, the first impurities diffusion layer, and the second impurity diffusion layer 51, wherein the gate electrode has a width that



continuously increase from a bottom thereof up to an upper surface thereof, wherein the semiconductor substrate has a first surface (top) and the indented section has a second surface below the first surface, and wherein the entire gate dielectric layer 124 is disposed on the second surface, wherein the sidewall dielectric layer 122A and the gate dielectric layer 124 are disposed in contact with the indented section, wherein the sidewall dielectric layer 122A surrounds the gate dielectric layer 124, wherein at a portion of the gate dielectric layer 124 is above at least a portion of the sidewall dielectric layer 122A

***Response to Arguments***

5. Applicant's arguments with respect to claims 1-12 have been considered but are moot in view of the new ground(s) of rejection.

***Conclusion***

6. Applicant's amendment necessitated the new ground(s) of rejection presented in this Office action. Accordingly, **THIS ACTION IS MADE FINAL**. See MPEP § 706.07(a). Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event,

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however, will the statutory period for reply expire later than SIX MONTHS from the date of this final action.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Thao X Le whose telephone number is 703-306-0208. The examiner can normally be reached on M-F from 8:00 AM - 4:30 PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Wael M Fahmy can be reached on 703-308-4918. The fax phone numbers for the organization where this application or proceeding is assigned are 703-308-7722 for regular communications and 703-308-7722 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is 703-308-0956.

Thao X. Le  
October 20, 2003



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